

ISO9001 & ISO14001 & TS16949 CHILISIN ELECTRONICS CORP. RoHS & Halogen Free & REACH Compliance.

SPECIFICATION FOR APPROVAL

Customer :			超利維			
Customer P/N:						
Drawing No:	IE1-8B0364					
Quantity :	Χ	Pcs.	DATE :	2018/11/16		
Chilisin P/N:		HEI	252008A-2R	2M-Q8		

	SPECIFICATION ACCEPTED BY:
COMPONENT	
ENGINEER	
ELECTRICAL	
ENGINEER	
MECHANICAL	
ENGINEER	
APPROVED	
REJECTED	

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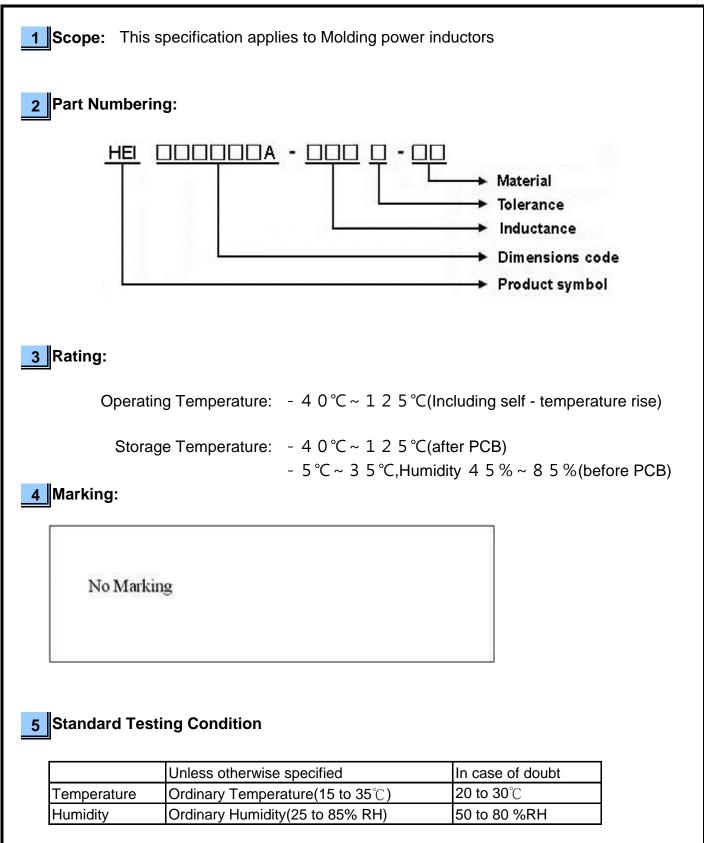
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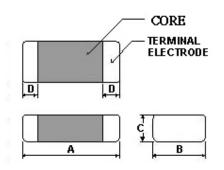






HEI252008A Series Specification

6 Configuration and Dimensions:



TYPE	ns in mm HEI252008A
А	2.5±0.3
В	2.0±0.3
С	0.8max
D	0.6±0.3

7 Electrical Characteristics:

Part No.	Inductance (uH)	Tolerance (±%)	Test Freq.	Irms(A) Max.(Typ)	Isat(A) Max.(Typ)	RDC(mΩ) Max.(Typ)	
HEI252008A-2R2M-Q8	2.2	20	2MHz,0.2V	1.3(1.6)	1.6(1.9)	184(160)	

NOTE:

1.Operating temperature range - 4 0 °C ~ 1 2 5 °C(Including self - temperature rise)

2.Isat for Inductance drop 30% from its value without current.

3.1rms for a 40°C temperature rise from 25°C ambient.

4.Rated current: Isat or Irms, whichever is smaller

5.All test data is referenced to 25 $^\circ\!\mathrm{C}$ ambient

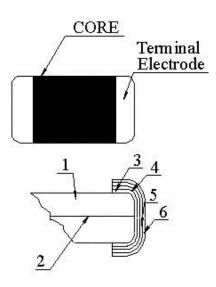
6.Absolute maximum voltage 20VDC



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HEI252008A Series Specification

8 HEI252008A Series 8.1 Construction:



8.2 Material List:

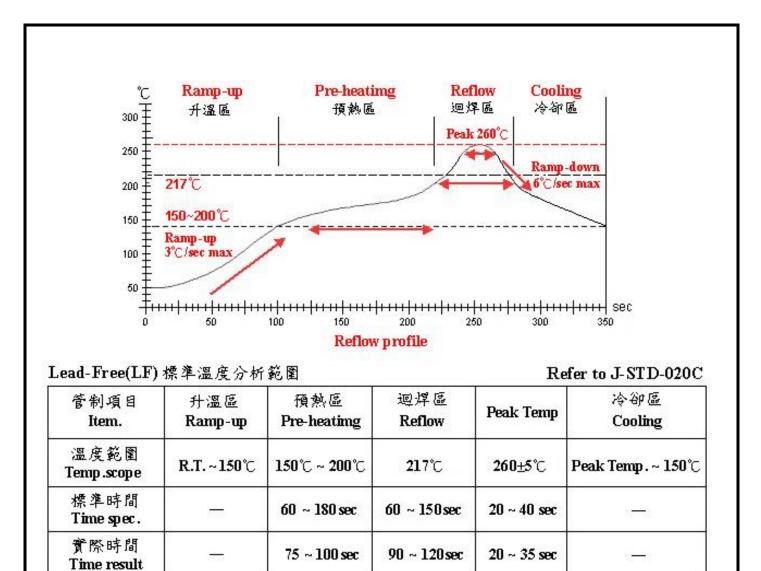
NO	Part	Description
1	Core	Metal Powder
2	Wire	Copper wire
3	Sputter/Plating	Cu
4	Silver Electrode	Ag
5	Plating	Ni
6	Plating	Sn



No	Nechanical Performance	Specification		Test Method	
	Flexure Strength	The forces applied on the right conditions must not damage the terminal electrode and the metal body	Test device shall be soldered on the substrate Substrate Dimension: 100x40x1.6mm		
-1-2	Vibration	Appearance:No damage (for microscope of CASTOR MZ-45 20X) Inductance change shall be within ±20%	Oscilla Amplit	evice shall be soldered on the substra tion Frequency: 10 to 55 to 10Hz for ude: 1.5mm 2hrs for each axis (X, Y & Z), total 6h	1min
-1-3	Resistance to Soldering Heat	Appearance: No damage More than 75% of the terminal. electrode should be covered with solder. Inductance: within ±20% of initial value	Pre-he Solder Solder	ating: 150℃, 1min Composition: Sn/Ag3.0/Cu0.5(Pb-Fr Temperature: 260±5℃ sion Time: 10±1sec	
-1-4	Solder ability	The electrodes shall be at least 95% covered with new solder coating	Pre-heating: 150℃, 1min Solder Composition: Sn/Ag3.0/Cu0.5(Pb-Free) Solder Temperature: 245±5℃ Immersion Time: 4±1sec		
-1-5	Terminal Strength Test	No split termination Chip F Mounting Pad	Test device shall be soldered on the substrate, then apply a force in the direction of the arrow. Force : 5N Keeping Time: 10±1sec		
-2.E	nvironmental Performance				
	Item	Specification		Test Method	
		Appearance: No damage	One cycle:		
	Temperature Cycle	Appearance. No damage		Tomporature (°C)	
	Temperature Cycle	Inductance:within±20% of	Step	Temperature (°C)	Time (mir
	Temperature Cycle	•	Step 1	-40±3	Time (mir 30
	Temperature Cycle	Inductance:within±20% of	1	-40±3 25±2	30 3
	Temperature Cycle	Inductance:within±20% of	1	-40±3	30 3 30
	Temperature Cycle	Inductance:within±20% of	1 2 3 4	-40±3 25±2 125±3 25±2	3
	Temperature Cycle	Inductance:within±20% of	1 2 3 4 Total:	-40±3 25±2 125±3 25±2 100cycles	30 3 30 30 3
-2-1		Inductance:within±20% of	1 2 3 4 Total: Measu	-40±3 25±2 125±3 25±2 100cycles ired after exposure in the room condit	30 3 30 30 3
-2-1	Temperature Cycle Humidity Resistance	Inductance:within±20% of	1 2 3 4 Total: Measu Tempe Relativ	-40±3 25±2 125±3 25±2 100cycles	30 3 30 30 3
-2-1		Inductance:within±20% of	1 2 3 Total: Measu Tempe Relativ Measu	-40 ± 3 25 ± 2 125 ± 3 25 ± 2 100cycles ured after exposure in the room condited after exposure in th	30 3 30 30 3
-2-1	Humidity Resistance High	Inductance:within±20% of	1 2 3 4 Total: Measu Relativ Measu Tempe	-40 ± 3 25 ± 2 125 ± 3 25 ± 2 100cycles ured after exposure in the room conditerature: $60\pm2^{\circ}C$ ve Humidity: 90 ~ 95% / Time: 500hrs ured after exposure in the room conditerature: $85\pm3^{\circ}C$	30 3 30 30 3
-2-1	Humidity Resistance	Inductance:within±20% of	1 2 3 4 Total: Measu Relativ Measu Tempe Relativ	-40 ± 3 25 ± 2 125 ± 3 25 ± 2 100cycles Ired after exposure in the room conditerature: $60\pm2^{\circ}C$ I/e Humidity: 90 ~ 95% / Time: 500hrs Ired after exposure in the room conditerature: $85\pm3^{\circ}C$ I/e Humidity: 0% / Time: 500hrs	30 3 30 30 3 ion for 24hr
-2-2	Humidity Resistance High Temperature Resistance	Inductance:within±20% of	1 2 3 4 Total: Measu Tempe Relativ Measu Measu	-40 ± 3 25 ± 2 125 ± 3 25 ± 2 100cycles Ired after exposure in the room condite erature: $60\pm2^{\circ}$ C /e Humidity: 90 ~ 95% / Time: 500hrs Ired after exposure in the room condite erature: $85\pm3^{\circ}$ C /e Humidity: 0% / Time: 500hrs Ired after exposure in the room condite erature: after exposure in the room condite	30 3 30 30 3 ion for 24hr
-2-1 -2-2	Humidity Resistance High	Inductance:within±20% of	1 2 3 4 Total: Measu Tempe Relativ Measu Tempe Relativ Measu Tempe	-40 ± 3 25 ± 2 125 ± 3 25 ± 2 100cycles Ired after exposure in the room conditerature: $60\pm2^{\circ}C$ I/e Humidity: 90 ~ 95% / Time: 500hrs Ired after exposure in the room conditerature: $85\pm3^{\circ}C$ I/e Humidity: 0% / Time: 500hrs	30 3 30 30 3 ion for 24hr



HEI252008A Series Specification



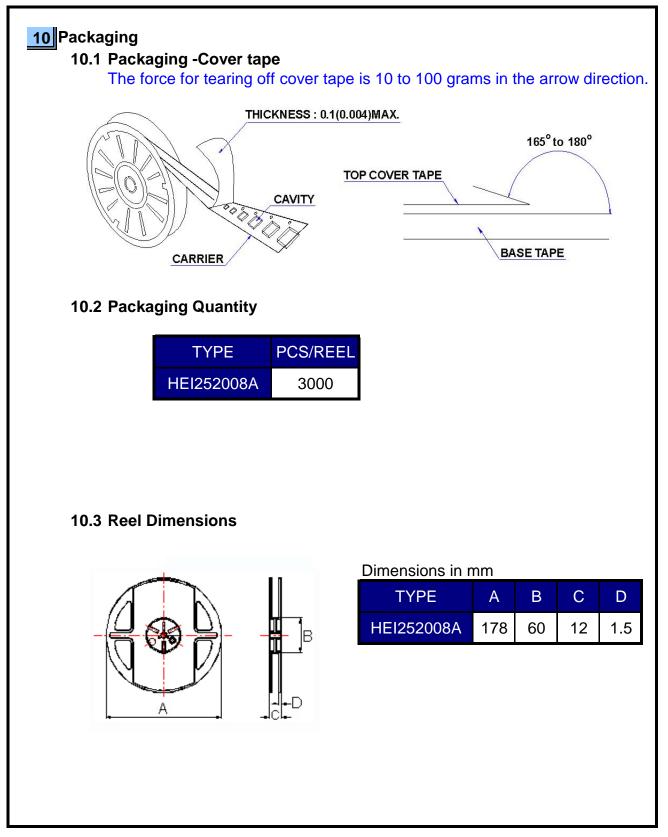
NOTE :

1. Re-flow possible times : within 2 times

2. Nitrogen adopted is recommended while in re-flow



TS16949 CHILISIN ELECTRONICS CORP.

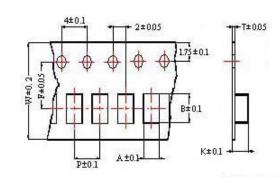




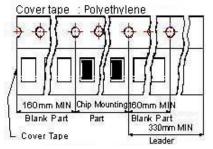
HEI252008A Series Specification

10 Packaging

10.4 Tape Dimensions in mm

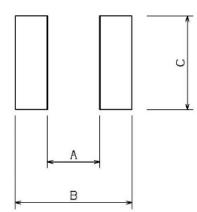


Tape Material Carrier tape : Polystyrene



TYPE	А	В	Т	W	Р	F	K
HEI252008A	2.25	2.8	0.22	8	4	3.5	1.05

11 Recommended Pattern



Dimensions in mm

TYPE	А	В	С
HEI252008A	1.2	2.8	2.3

12 Note:

- 1. Please make sure that your product has been evaluated and confirmed against your specifications when our product is mounted to your product.
- 2. Do not knock nor drop.
- 3. All the items and parameters in this product specification have been prescribed on the premise that our product is used for the purpose, under the condition and in the environment agreed upon between you and us. You are requested not to use our product deviating from such agreement.
- 4. Please keep the distance between transformer/coil and other components (refer to the standard IEC 950)
- 5.After manufacturing process, there might be slight irregular shape on the edge of the products, and it's a normal phenomenon that can be neglected
- 6. The moisture sensitivity level (MSL) of products is classified as level 1.



